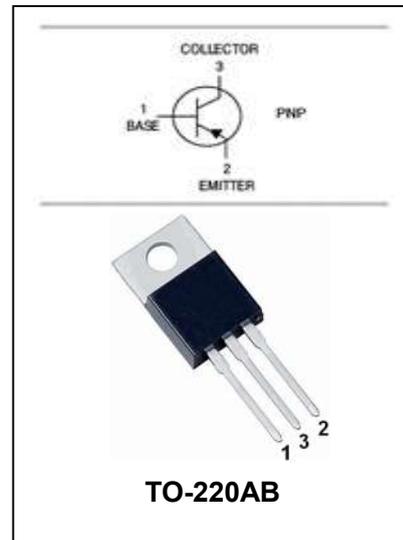


PNP Epitaxial Silicon Transistor

2SB507

FEATURES

- Low Frequency Power Amplifier.
- Complements the 2SD313.



MAXIMUM RATING operating temperature range applies unless otherwise specified

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-7	V
I_C	Collector Current	-3	A
P_C	Collector Dissipation	30	W
T_j, T_{stg}	Junction and Storage Temperature	-50 to +150	°C

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ELECTRICAL CHARACTERISTICS Ratings at 25°C ambient temperature unless otherwise specified.

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=-60V, I_E=0$			-100	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=-7V, I_C=0$			-100	μA
DC Current Gain	h_{FE}	$V_{CE}=-2V, I_C=-1A$	40		320	
Collector-emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-2A, I_B=-0.2A$			-1	V
Transition Frequency	f_T	$V_{CE}=-5V, I_E=-0.5A$		8		MHz

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PACKAGE OUTLINE

Plastic surface mounted package

TO-220AB

